

L-32P3C

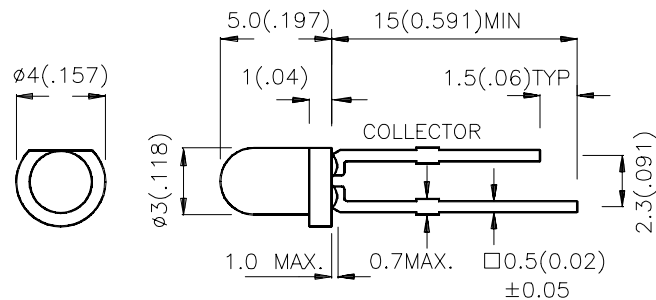
Features

- MECHANICALLY AND SPECTRALLY MATCHED TO THE L34 SERIES INFRARED EMITTING LED LAMP.
- WATER CLEAR LENS.

Description

Made with NPN silicon phototransistor chips.

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25(0.01)$ unless otherwise noted.
3. Lead spacing is measured where the lead emerge package.
4. Specifications are subjected to change without notice.

Absolute Maximum Rating at $T_A=25^{\circ}\text{C}$

Parameter	Maximum Ratings
Collector-to-Emitter Breakdown Voltage	30V
Emitter-to-Collector Breakdown Voltage	5V
Power Dissipation at (or below) 25°C Free Air Temperature	100mW
Operating Temperature Range	$-40^{\circ}\text{C} \sim +85^{\circ}\text{C}$
Storage Temperature Range	$-40^{\circ}\text{C} \sim +85^{\circ}\text{C}$
Lead Soldering Temperature(4mm For 5sec)	260°C

Electrical And Radiant Characteristics at $T_A=25^{\circ}\text{C}$

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
$V_{BR\ CE0}$	Collector-to-Emitter Breakdown Voltage	30	-	-	V	$I_C=100\mu\text{A}$ $E_e=0\text{mW}/\text{cm}^2$
$V_{BR\ ECO}$	Emitter-to-Collector Breakdown Voltage	5	-	-	V	$I_E=100\mu\text{A}$ $E_e=0\text{mW}/\text{cm}^2$
$V_{CE\ (SAT)}$	Collector-to-Emitter Saturation Voltage	-	-	0.8	V	$I_C=2\text{mA}$ $E_e=20\text{mW}/\text{cm}^2$
I_{CE0}	Collector Dark Current	-	-	100	nA	$V_{CE}=10\text{V}$ $E_e=0\text{mW}/\text{cm}^2$
T_R	Rise Time (10% to 90%)	-	3	-	us	$V_{CE}=5\text{V}$ $I_C=1\text{mA}$ $R_L=1\text{K}\Omega$
T_F	Fall Time (90% to 10%)	-	3	-	us	
$I_{(ON)}$	On State Collector Current	0.1	0.5	-	mA	$V_{CE}=5\text{V}$, $E_e=1\text{mW}/\text{cm}^2$, $\lambda=940\text{nm}$